

ABSTRACT

There is included (a) forming a chlorine-containing semiconductor layer on an insulating film provided on a surface of a substrate by supplying a first gas containing a semiconductor element and chlorine to the substrate; and (b) forming a semiconductor film on the chlorine-containing semiconductor layer by supplying a second gas containing a semiconductor element to the substrate, wherein a chlorine concentration in the chlorine-containing semiconductor layer formed in (a) is made 1.0×10^{20} atoms/cm³ or more and 1.0×10^{22} atoms/cm³ or less.

FIGURE 4